

IN THE SPECIFICATION:

Please rewrite the two new paragraphs that were added at the end of page 6 or top of page 7, by the Amendment filed July 12, 2005, so that they read as follows:

In Figs. 3(a)- 3(c), the line break on the right side indicates that region 6 may extend horizontally in the figures farther than is shown, such that an area of the region 6 would be greater than an area of the region 4 and/or region 5. Even without taking the break into account, shown. Fig. 3(c) shows that the area occupied by the etched non-doped polysilicon region 6 dummy gate pattern is larger than the total area occupied by the N-type and P-type polysilicon regions gates which have been etched.

Figs. 3(a)- 3(c) also show how the regions are contiguous.